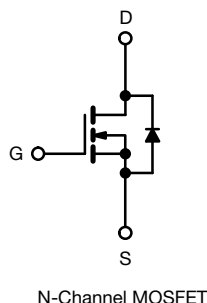
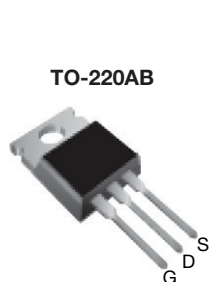


Power MOSFET



FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptable power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Two transistor forward
- Half bridge
- Full bridge

PRODUCT SUMMARY

V_{DS} (V)	500
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 3.0
Q_g (Max.) (nC)	17
Q_{gs} (nC)	4.3
Q_{gd} (nC)	8.5
Configuration	Single

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF820APbF
Lead (Pb)-free and halogen-free	IRF820APbF-BE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	500	V
Gate-source voltage	V_{GS}	± 30	
Continuous drain current	I_D	2.5	A
		1.6	
Pulsed drain current ^a	I_{DM}	10	
Linear derating factor		0.40	W/ $^\circ\text{C}$
Single pulse avalanche energy ^b	E_{AS}	140	mJ
Repetitive avalanche current ^a	I_{AR}	2.5	A
Repetitive avalanche energy ^a	E_{AR}	5.0	mJ
Maximum power dissipation	P_D	50	W
Peak diode recovery dV/dt ^c	dV/dt	3.4	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) ^d		300 ^d	
Mounting torque		10	lbf · in
		1.1	N · m


Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 45\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 2.5\text{ A}$ (see fig. 12)
- $I_{SD} \leq 2.5\text{ A}$, $dI/dt \leq 270\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

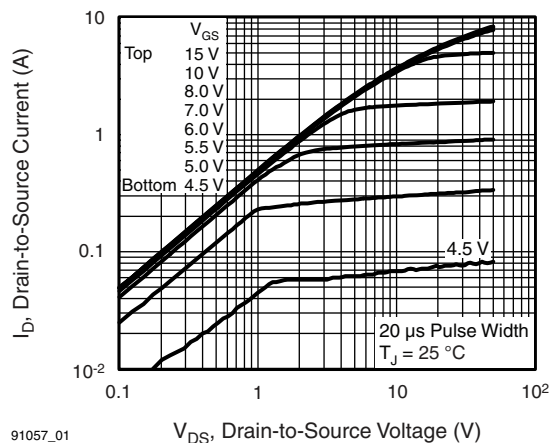
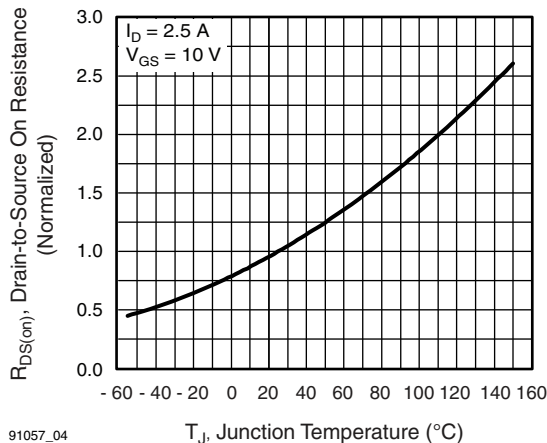
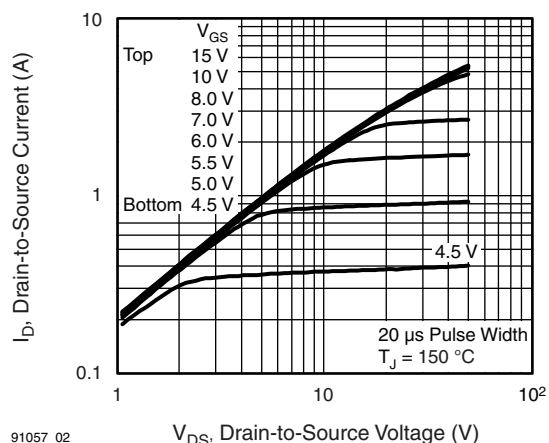
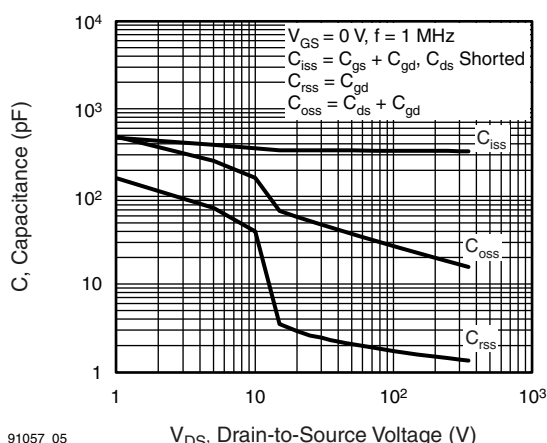
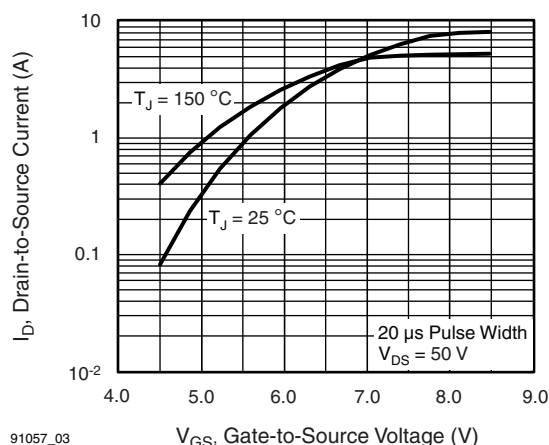
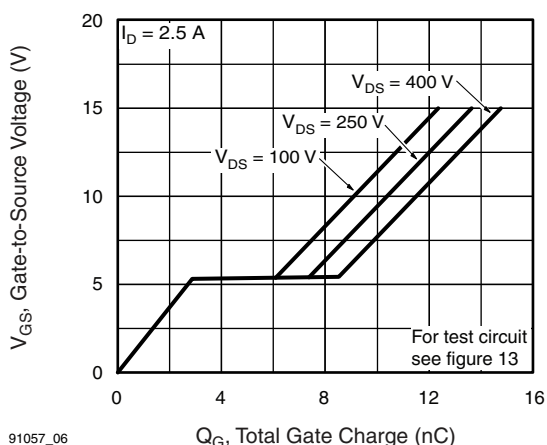
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	2.5	

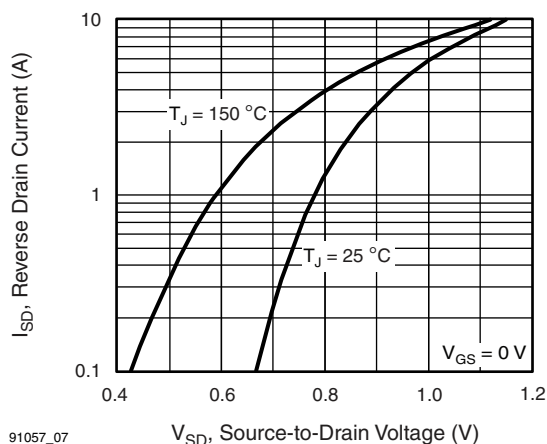
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		500	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.60	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.5	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 30 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 1.5 A ^b	-	-	3.0	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 1.5 A ^b		1.4	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	340	-	pF
Output capacitance	C _{oss}			-	53	-	
Reverse transfer capacitance	C _{rss}			-	2.7	-	
Output capacitance	C _{oss}	V _{GS} = 0 V; V _{DS} = 1.0 V, f = 1.0 MHz			490		
Output capacitance	C _{oss}	V _{GS} = 0 V; V _{DS} = 400 V, f = 1.0 MHz			15		
Effective output capacitance	C _{oss} eff.	V _{GS} = 0 V; V _{DS} = 0 V to 400 V ^c			28		
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 2.5 A, V _{DS} = 400 V, see fig. 6 and 13 ^b	-	-	17	nC
Gate-source charge	Q _{gs}			-	-	4.3	
Gate-drain charge	Q _{gd}			-	-	8.5	
Turn-on delay time	t _{d(on)}	V _{DD} = 250 V, I _D = 2.5 A, R _g = 21 Ω, R _D = 97 Ω, see fig. 10 ^b		-	8.1	-	ns
Rise time	t _r			-	12	-	
Turn-Off delay time	t _{d(off)}			-	16	-	
Fall time	t _f			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	2.5	A
Pulsed diode forward current ^a	I _{SM}			-	-	10	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 2.5 A, V _{GS} = 0 V ^b		-	-	1.6	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 2.5 A, dI/dt = 100 A/μs ^b		-	330	500	ns
Body diode reverse recovery charge	Q _{rr}			-	760	1140	nC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

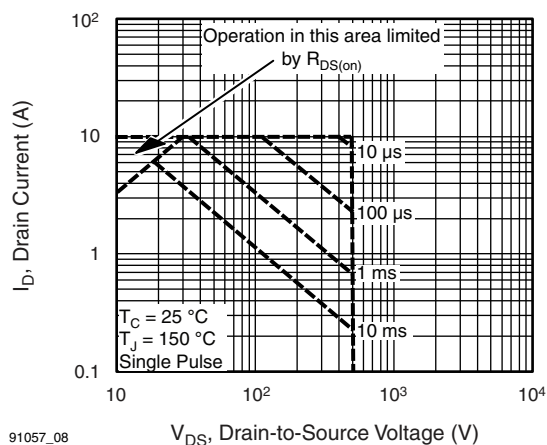
Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

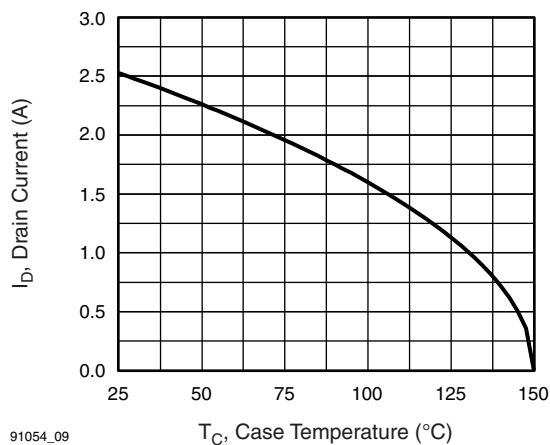
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



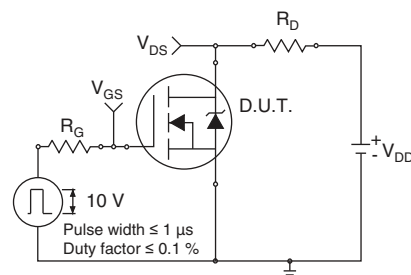
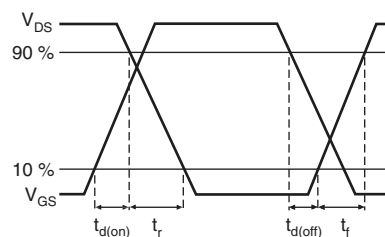
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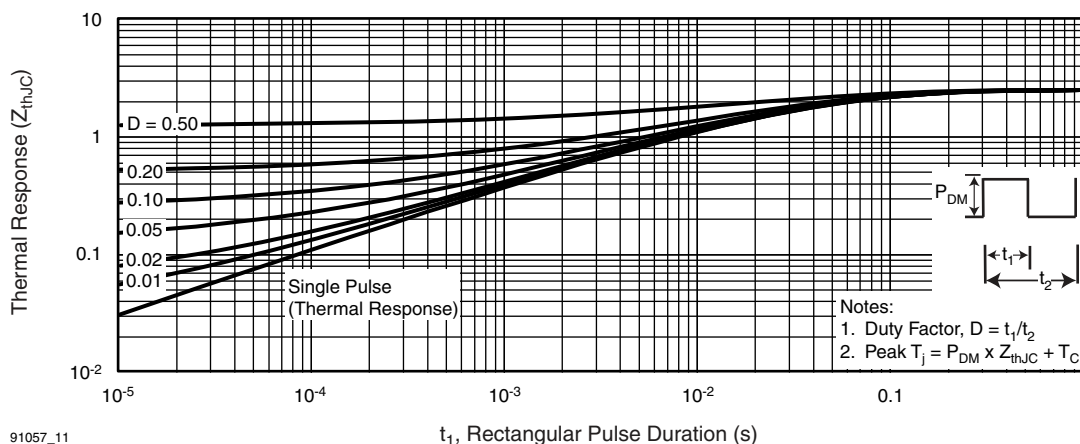
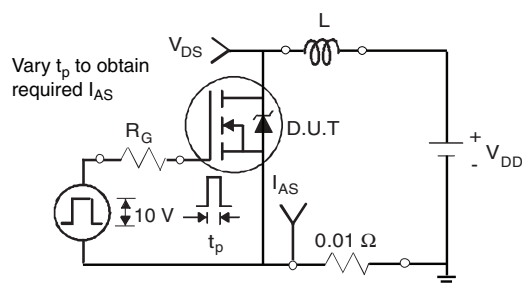
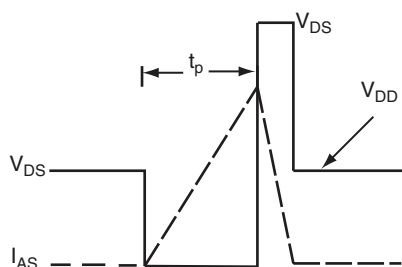
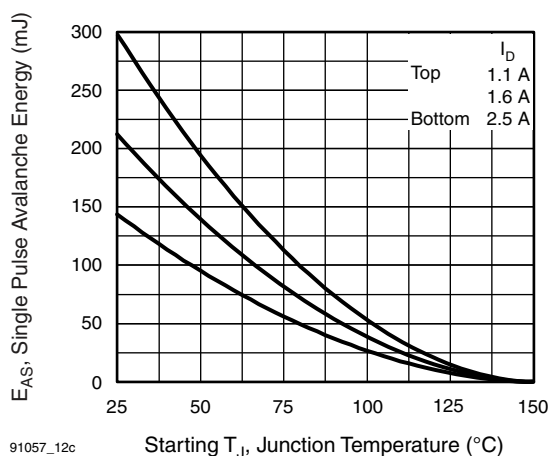
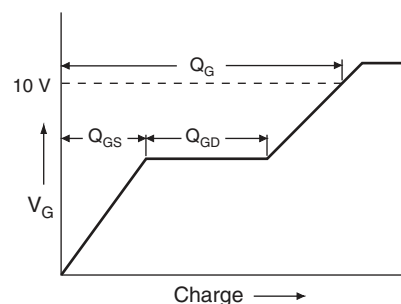
Fig. 7 - Typical Source-Drain Diode Forward Voltage


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Fig. 8 - Maximum Safe Operating Area


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Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10 - Switching Time Test Circuit

Fig. 11 - Switching Time Waveforms


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 13 - Unclamped Inductive Test Circuit

Fig. 14 - Unclamped Inductive Waveforms

Fig. 15 - Maximum Avalanche Energy vs. Drain Current

Fig. 16 - Basic Gate Charge Waveform

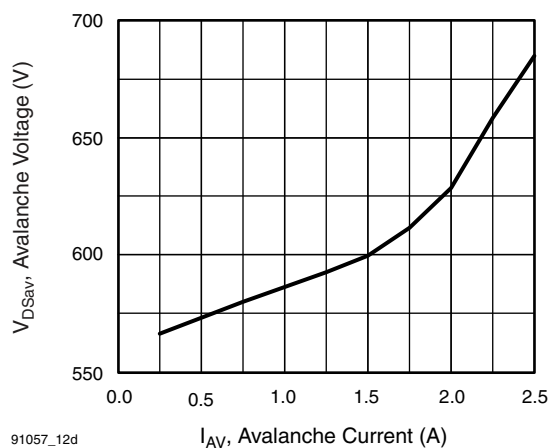


Fig. 17 - Typical Drain-to-Source Voltage vs. Avalanche Current

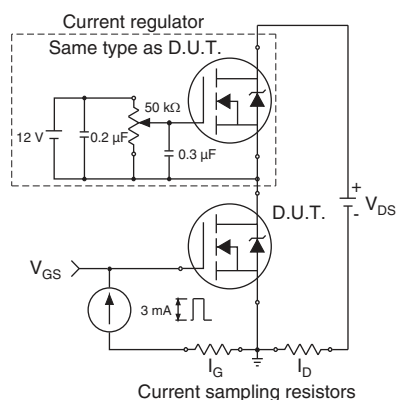
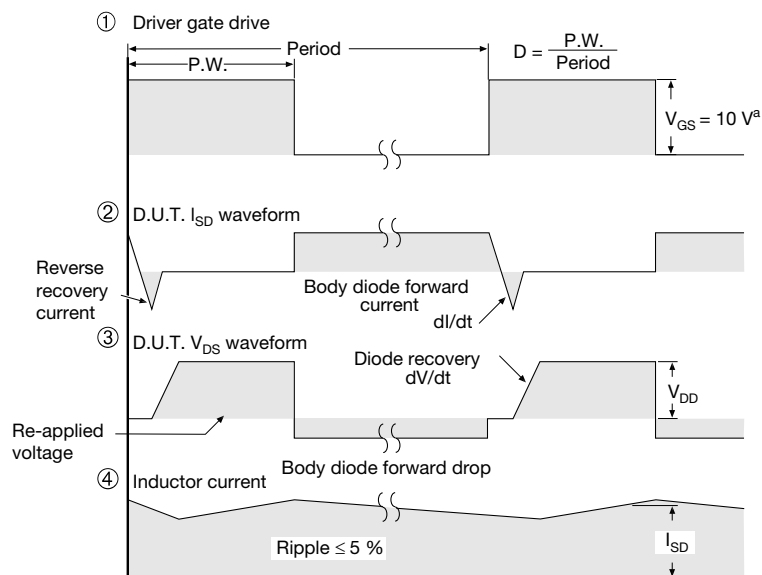
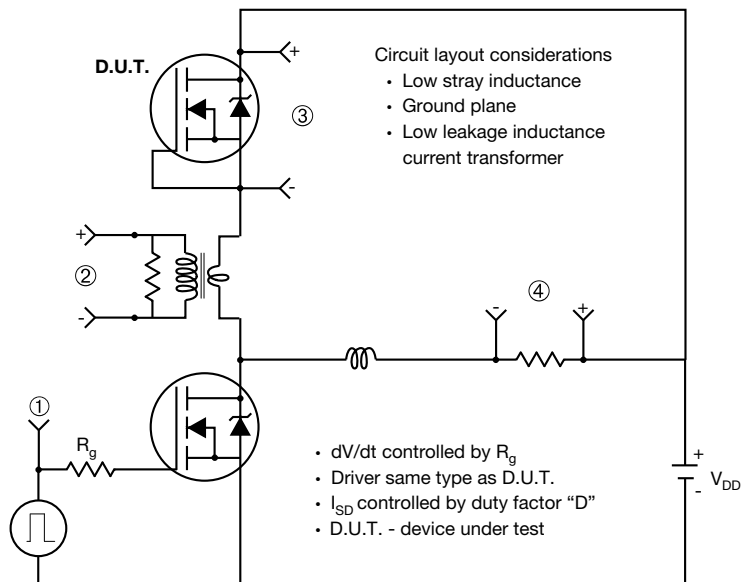


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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